



STG4260

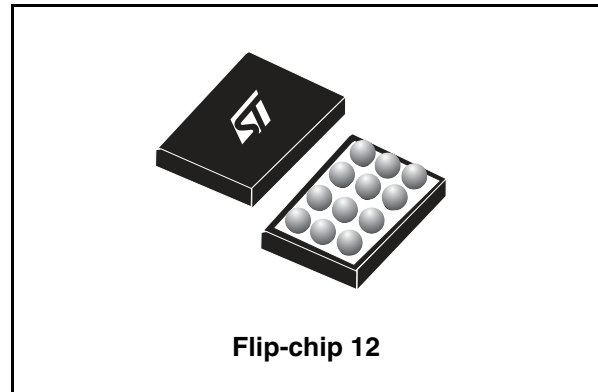
Low voltage 0.5 Ω dual SPDT switch with break-before-make feature and 15 kV ESD protection

Features

- Wide operating voltage range:
 V_{CC} (OPR) = 1.65 to 4.8 V
- Low power dissipation:
 I_{CC} = 0.2 μ A (max.) at T_A = 85 °C
- Low "ON" resistance:
 - R_{ON} = 0.75 Ω (T_A = 25 °C) at V_{CC} = 2.25 V
 - R_{ON} = 0.50 Ω (T_A = 25 °C) at V_{CC} = 3.0 V
 - R_{ON} = 0.40 Ω (T_A = 25 °C) at V_{CC} = 4.3 V
- Separate supply voltage for switch and control pin
- Latch-up performance exceeds 100 mA per JESD 78, Class II
- ESD performance tested on common pin (D pin):
 - 15 kV IEC-61000-4-2 ESD, contact discharge
 - 8 kV HBM JESD22 A114-B Class II
- ESD performance tested on S1 and S2 pin:
 - 8 kV IEC-61000-4-2 ESD, contact discharge
- ESD performance test on all other pins:
 - 4 kV HBM (JESD22 A114-B Class II)
 - 400 V machine model (JESD22 A115-A)
 - 1500 V charged-device model (JESD22 C101)

Applications

- Mobile phones



Description

The STG4260 is a high-speed CMOS low voltage dual analog SPDT (single pole dual throw) switch or 2:1 multiplexer/demultiplexer switch fabricated in silicon gate C²MOS technology. It is designed to operate from 1.65 V to 4.8 V, making this device ideal for portable applications. It offers low ON-resistance (0.40 Ω typ.) at V_{CC} = 4.3 V. The SEL inputs are provided to control the switches.

The switch S1 is ON (connected to common port D) when the SEL input is held high and OFF (high impedance state exists between the two ports) when SEL is held low; the switch S2 is ON (it is connected to common Port D) when the SEL input is held low and OFF (high impedance state exists between the two ports) when SEL is held high.

Additional key features are fast switching speed, break-before-make delay time and ultra low power consumption. All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

Table 1. Device summary

Order code	Package	Packing
STG4260BJR	Flip-chip 12	Tape and reel

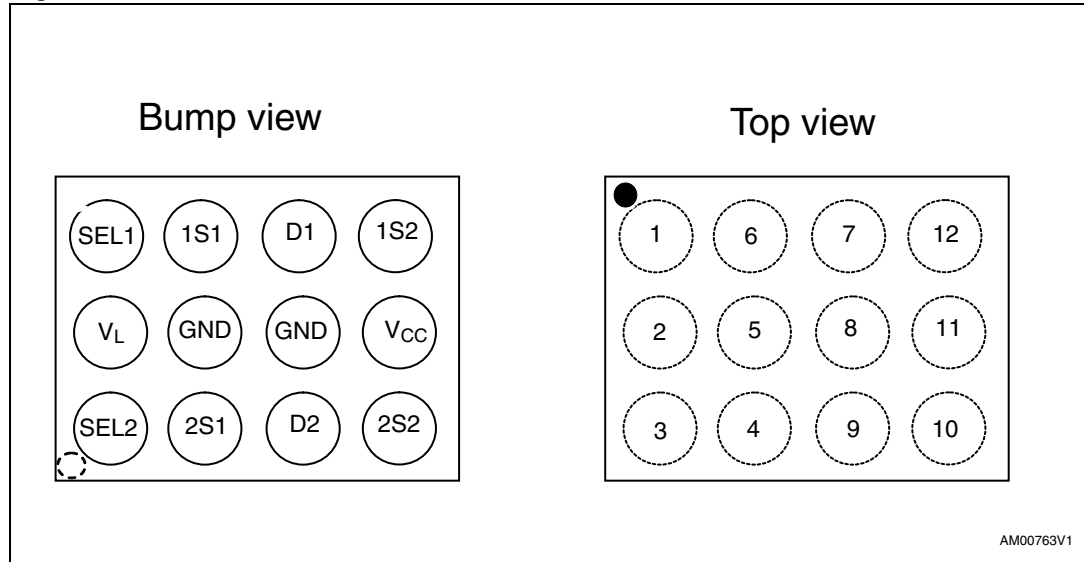
Contents

1	Pin settings	3
	1.1 Pin connections	3
	1.2 Pin description	3
2	Logic diagram	4
3	Maximum ratings	5
4	Electrical characteristics	6
5	Test circuits	10
6	Package mechanical data	14
7	Revision history	18

1 Pin settings

1.1 Pin connections

Figure 1. Pin connection



AM00763V1

1.2 Pin description

Table 2. Pin assignment

Pin number	Symbol	Name and function
1	SEL2	Selection control for switch 2
2	V _L	Logic supply voltage
3	SEL1	Selection control for switch 1
4	1S1	Independent channel for switch 1
5	GND	Ground (0 V)
6	2S1	Independent channel for switch 2
7	D2	Common channel for switch 2
8	GND	Ground (0 V)
9	D1	Common channel for switch 1
10	1S2	Independent channel for switch 1
11	V _{CC}	Positive supply voltage
12	2S2	Independent channel for switch 2

2 Logic diagram

Figure 2. Functional diagram

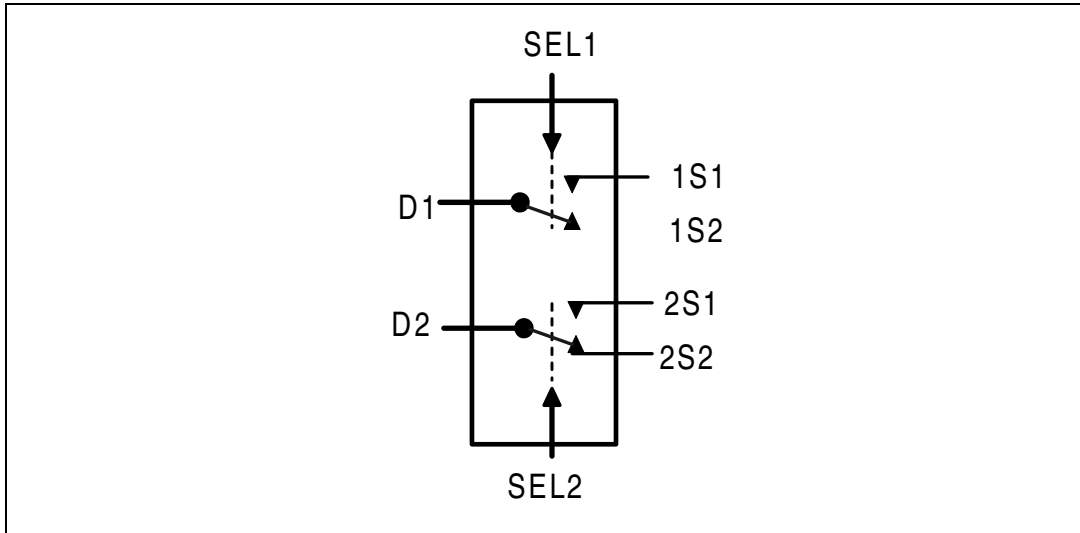


Figure 3. Circuit equivalent logic

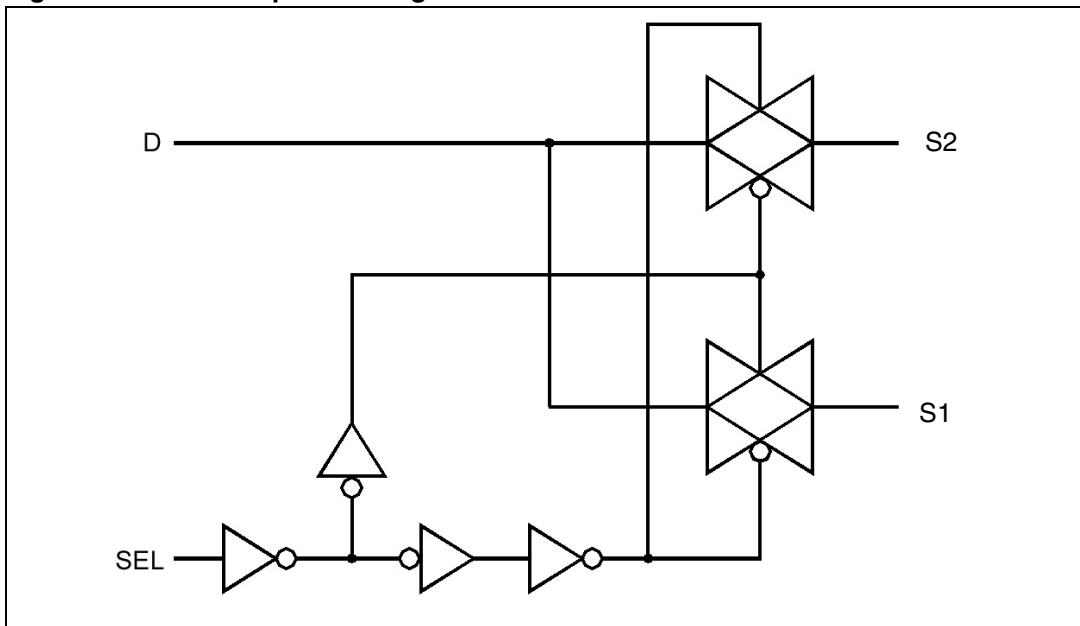


Table 3. Truth table

SEL	Switch S1	Switch S2
H	ON	OFF ⁽¹⁾
L	OFF ⁽¹⁾	ON

1. High impedance

3 Maximum ratings

Stressing the device above the rating listed in the “Absolute maximum ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute maximum rating conditions for extended periods may affect device reliability.

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	-0.5 to 5.5	V
V_L	Logic supply voltage	-0.5 to 5.5	V
V_I	DC input voltage	-0.5 to $V_{CC} + 0.5$	V
V_{IC}	DC control input voltage	-0.5 to $V_L + 5.5$	V
V_O	DC output voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IKC}	DC input diode current on control pin ($V_{SEL} < 0$ V)	- 50	mA
I_{IK}	DC input diode current ($V_{SEL} < 0$ V)	± 50	mA
I_{OK}	DC output diode current	± 20	mA
I_O	DC output current	± 300	mA
I_{OP}	DC output current peak (pulse at 1ms, 10% duty cycle)	± 500	mA
I_{CC} or I_{GND}	DC V_{CC} or ground current	± 100	mA
P_D	Power dissipation at $T_A = 70^\circ\text{C}$ ⁽¹⁾	500	mW
T_{stg}	Storage temperature	-65 to 150	$^\circ\text{C}$
T_L	Lead temperature (10 sec)	260	$^\circ\text{C}$

1. Derate above 70 $^\circ\text{C}$ by 18.5 mW/ $^\circ\text{C}$

Table 5. Recommended operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	1.65 to 4.8	V
V_L	Logic supply voltage ⁽¹⁾	1.65 to V_{CC}	V
V_I	Input voltage	0 to V_{CC}	V
V_{IC}	Control input voltage	0 to V_L	V
V_O	Output voltage	0 to V_{CC}	V
T_{op}	Operating temperature	-40 to 85	$^\circ\text{C}$
dt/dv	Input rise and fall time control input	$V_L = 1.65$ to 2.7 V	0 to 20
		$V_L = 3.0$ to 4.8 V	0 to 10

1. V_L pin should not be left floating.

4 Electrical characteristics

Table 6. DC specifications

Symbol	Parameter	V _{CC} (V)	V _L (V)	Test condition	Value					Unit
					T _A = 25 °C			-40 to 85 °C		
					Min	Typ	Max	Min	Max	
V _{IH}	High level input voltage	1.65 – 4.3	1.65 – 1.95		1.25	–	–	1.25	–	V
			2.3 – 2.7		1.75	–	–	1.75	–	
			3.0 – 3.6		2.34	–	–	2.34	–	
			4.3		2.80	–	–	2.80	–	
V _{IL}	Low level input voltage	1.65 – 4.3	1.65 – 1.95		–	–	0.6	–	0.6	V
			2.3 – 2.7		–	–	0.8	–	0.8	
			3.0 – 3.6		–	–	1.05	–	1.05	
			4.3		–	–	1.5	–	1.5	
R _{ON}	ON resistance	1.8	1.65 – 4.3	V _S = 0 V to V _{CC} I _S = 100 mA	–	1.5	2.5	–	3.7	Ω
		2.25			–	0.75	1.0	–	1.3	
		3			–	0.50	0.65	–	0.8	
		3.7			–	0.45	0.55	–	0.7	
		4.3			–	0.40	0.50	–	0.65	
ΔR _{ON}	ON resistance match between channels ⁽¹⁾	1.8	1.65 – 4.3	V _S = 0 V to V _{CC} I _S = 100 mA	–	40	–	–	–	mΩ
		2.25			–	20	–	–	–	
		3			–	10	–	–	–	
		3.7			–	10	–	–	–	
		4.3			–	10	–	–	–	
R _{FLAT}	ON resistance flatness ⁽²⁾	1.8	1.65 – 4.3	V _S = 0 V to V _{CC} I _S = 100 mA	–	1000	1700	–	2000	mΩ
		2.25			–	300	430	–	550	
		3			–	170	220	–	270	
		3.7			–	160	210	–	270	
		4.3			–	160	210	–	270	
I _{OFF}	Sn OFF state leakage current	4.3	4.3	V _S = 0.3 to 4.0 V _D = 0.3 to 4.0	-30	–	30	-300	300	nA
I _{ON}	Sn ON state leakage current	4.3	4.3	V _S = 0.3 to 4.0 V _D = open	-30	–	30	-300	300	nA
I _D	D ON state leakage current	4.3	4.3	V _S = open V _D = 0.3 to 4.0	-30	–	30	-300	300	nA

Table 6. DC specifications (continued)

Symbol	Parameter	V _{CC} (V)	V _L (V)	Test condition	Value					Unit
					T _A = 25 °C			-40 to 85 °C		
					Min	Typ	Max	Min	Max	
I _{CC}	Quiescent supply current	1.65 – 4.3	1.65 – 4.3	V _{SEL} = V _{CC} or GND	-0.05	–	0.05	-0.2	0.2	μA
I _{SEL}	SEL leakage current	1.65 – 4.3	1.65 – 4.3	V _{SEL} = 4.3V or GND	-0.2	–	0.2	-2	2	μA

1. $\Delta R_{ON} = R_{ON(Max)} - R_{ON(Min)}$
2. Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.

Table 7. AC electrical characteristics (C_L = 35 pF, R_L = 50 Ω, t_r = t_f ≤ 5 ns)

Symbol	Parameter	V _{CC} (V)	V _L (V)	Test conditions	Value					Unit
					T _A = 25 °C			-40 to 85 °C		
					Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation delay	1.65-1.95	1.65 – 4.3		–	0.18	–	–	–	ns
		2.3 – 2.7			–	0.14	–	–		
		3.0 – 3.3			–	0.12	–	–		
		3.6 – 4.3			–	0.12	–	–		
t _{ON}	TURN-ON time	1.65 – 1.95	1.65 – 4.3	V _S = V _{CC} R _L = 50 Ω C _L = 30 pF	–	70	123	–	160	ns
		2.3 – 2.7			–	48	62	–	80	
		3 – 3.6			–	33	43	–	56	
		4.3			–	29	38	–	49	
t _{OFF}	TURN-OFF time	1.65 – 1.95	1.65 – 4.3	V _S = V _{CC} R _L = 50 Ω C _L = 30 pF	–	36	45	–	60	ns
		2.3 – 2.7			–	35	47	–	62	
		3 – 3.6			–	30	40	–	51	
		4.3			–	29	38	–	50	
t _D	Break-before- make time delay	1.65 – 1.95	1.65 – 4.3	C _L = 35 pF R _L = 50 Ω V _S = V _{CC} /2	10	42	–	–	–	ns
		2.3 – 2.7			10	22	–	–	–	
		3 – 3.6			5	15	–	–	–	
		4.3			5	12	–	–	–	

Table 7. AC electrical characteristics ($C_L = 35 \text{ pF}$, $R_L = 50 \text{ } \Omega$, $t_r = t_f \leq 5 \text{ ns}$) (continued) (continued)

Symbol	Parameter	V _{CC} (V)	V _L (V)	Test conditions	Value					Unit
					T _A = 25°C			-40 to 85°C		
					Min	Typ	Max	Min	Max	
Q	Charge injection	1.65 – 1.95	1.65-4.3	C _L = 1nF V _{GEN} = 0 V	–	83	–	–	–	pC
		2.3 – 2.7			–	98	–	–		
		3.0 – 3.3			–	114	–	–		
		3.6 – 4.3			–	140	–	–		
OIRR	Off isolation ⁽¹⁾	1.65 – 4.3	4.3	V _S = 1V _{RMS} f = 100 kHz	–	77	–	–	–	dB
				V _S = 1V _{RMS} f = 1 MHz	–	67	–	–	–	
				V _S = 1V _{RMS} f = 5 MHz	–	50	–	–	–	
Xtalk	Crosstalk	1.65 – 4.3	4.3	V _S = 1V _{RMS} f = 100 kHz	–	80	–	–	–	dB
				V _S = 1V _{RMS} f = 1 MHz	–	67	–	–	–	
				V _S = 1V _{RMS} f = 5 MHz	–	50	–	–	–	
THD	Total harmonic distortion	2.3 – 4.3	4.3	R _L = 600 Ω C _L = 50 pF V _S = V _{CC} V _{PP} f = 600 Hz to 20 kHz	–	0.01	–	–	–	%
BW	-3dB bandwidth (switch ON)	1.65 – 4.3	4.3	R _L = 50 Ω	–	50	–	–	–	MHz

1. OFF-isolation = 20 log₁₀ (V_D/V_S), V_D = output, V_S = input to off switch

Table 8. Capacitive characteristics

Symbol	Parameter	V _{CC} (V)	V _L (V)	Test condition	Value					Unit
					T _A = 25 °C			-40 to 85 °C		
					Min	Typ	Max	Min	Max	
C _{SEL}	Control pin input capacitance	1.8 – 4.3	1.8 – 4.3	V _L = V _{CC}	–	30	–	–	–	pf
C _{SN}	Sn port capacitance	1.8 – 4.3	1.8 – 4.3	V _L = V _{CC}	–	94	–	–	–	pf
C _D	D port capacitance when the switch is enabled	1.8 – 4.3	1.8 – 4.3	V _L = V _{CC}	–	227	–	–	–	pf

Figure 6. OFF leakage

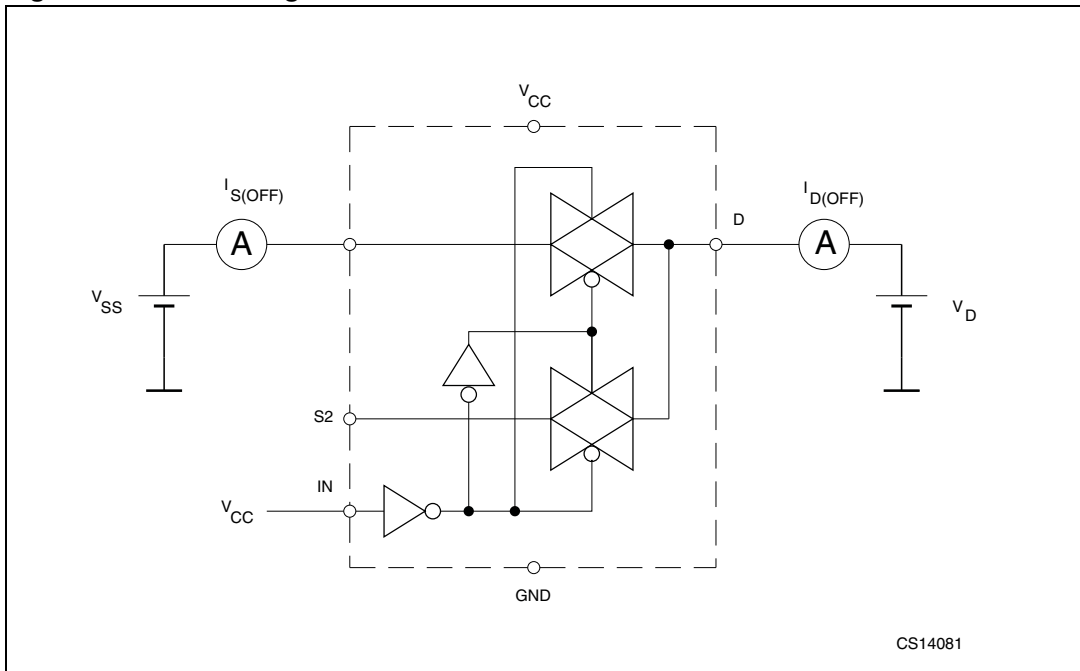


Figure 7. Channel-to-channel crosstalk

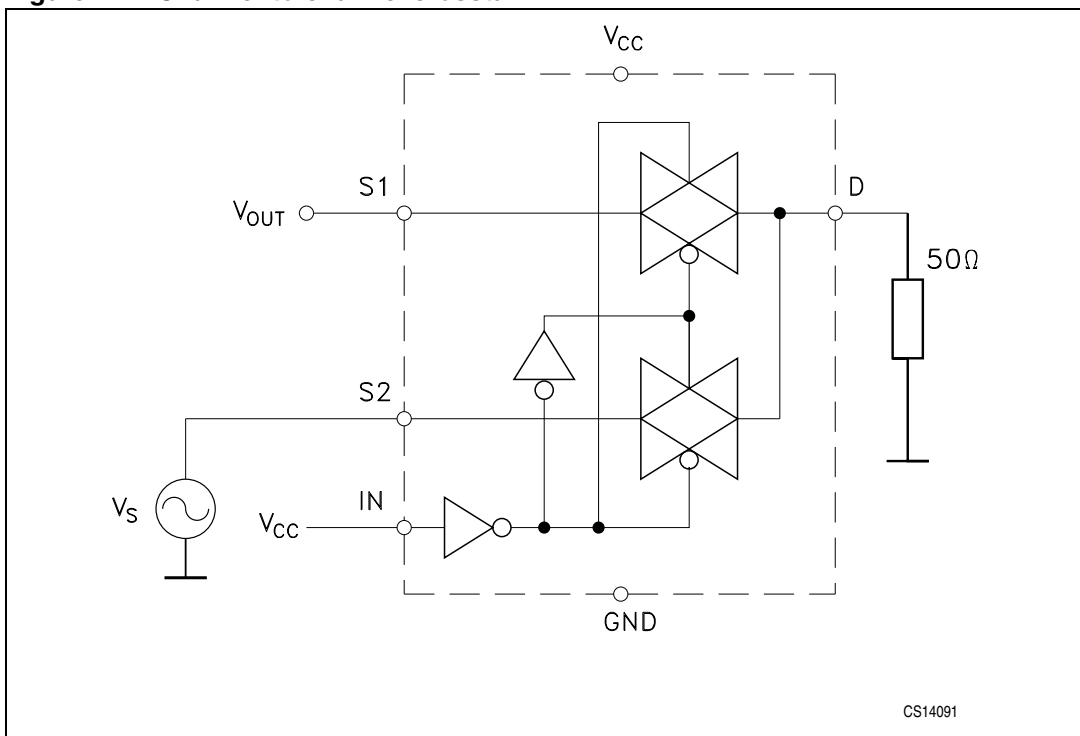
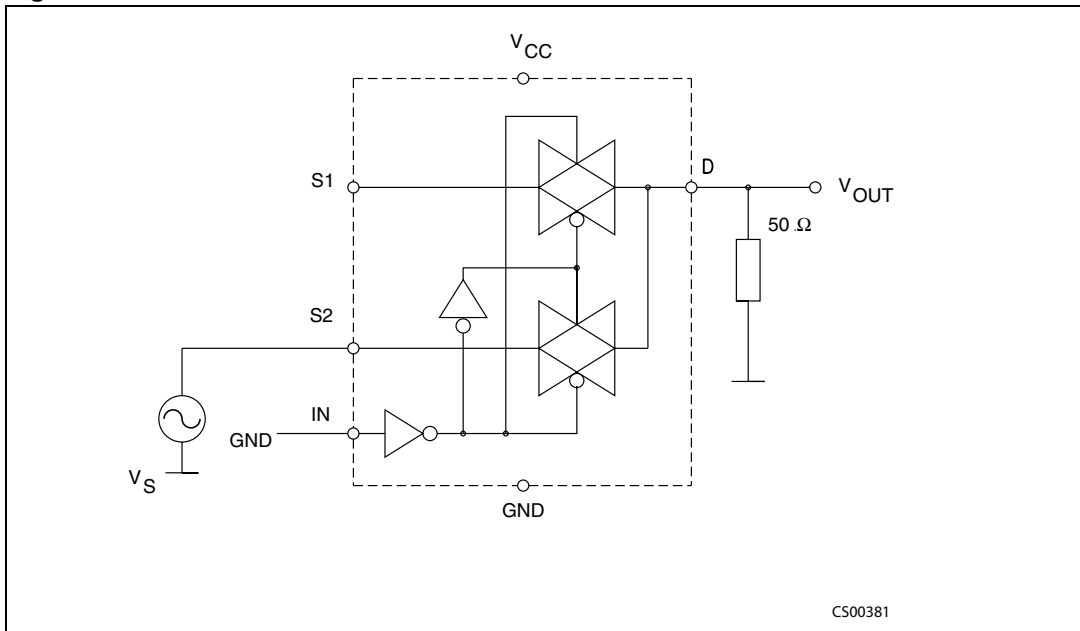
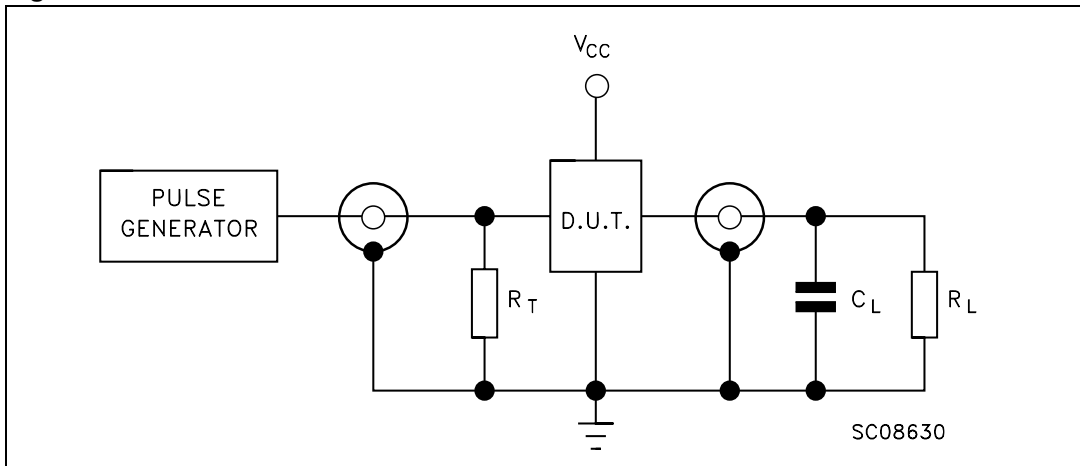


Figure 8. OFF isolation



CS00381

Figure 9. Test circuit



SC08630

1. $C_L = 5/35$ pF or equivalent: (includes jig capacitance)
2. $R_L = 50 \Omega$ or equivalent
3. $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

Figure 10. Break-before-make time delay

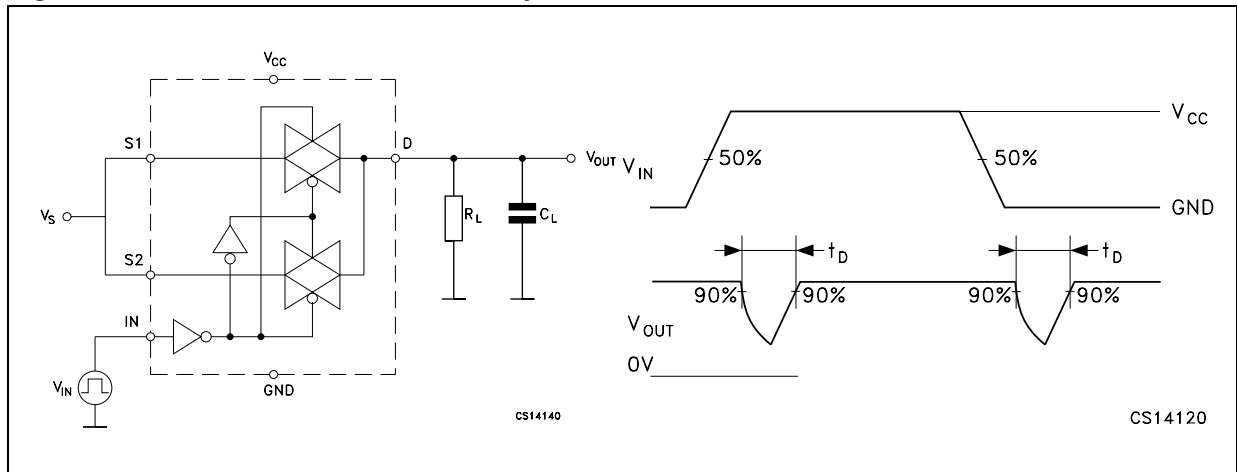


Figure 11. Switching time and charge injection
 ($V_{GEN} = 0\text{ V}$, $R_{GEN} = 0\ \Omega$, $R_L = 1\text{ M}\Omega$, $C_L = 100\text{ pF}$)

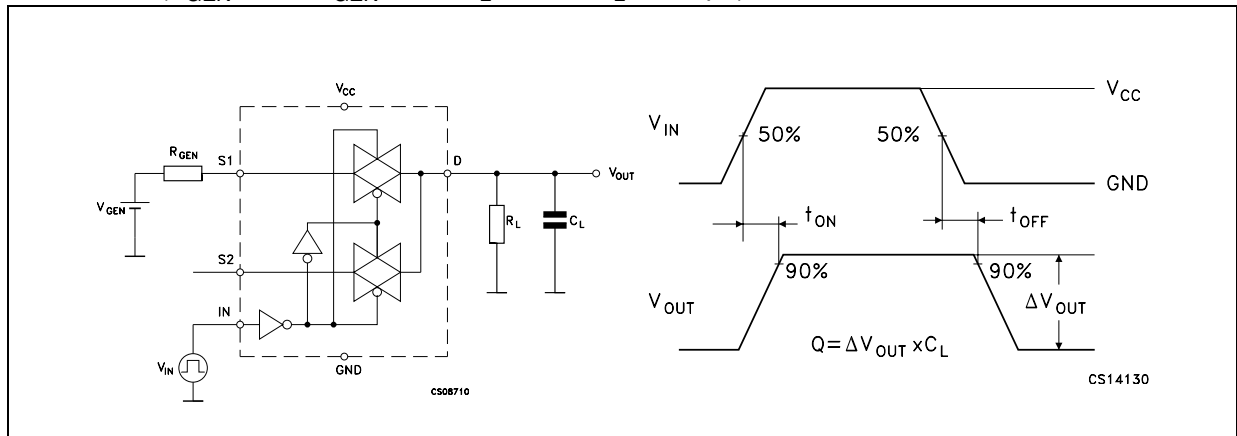
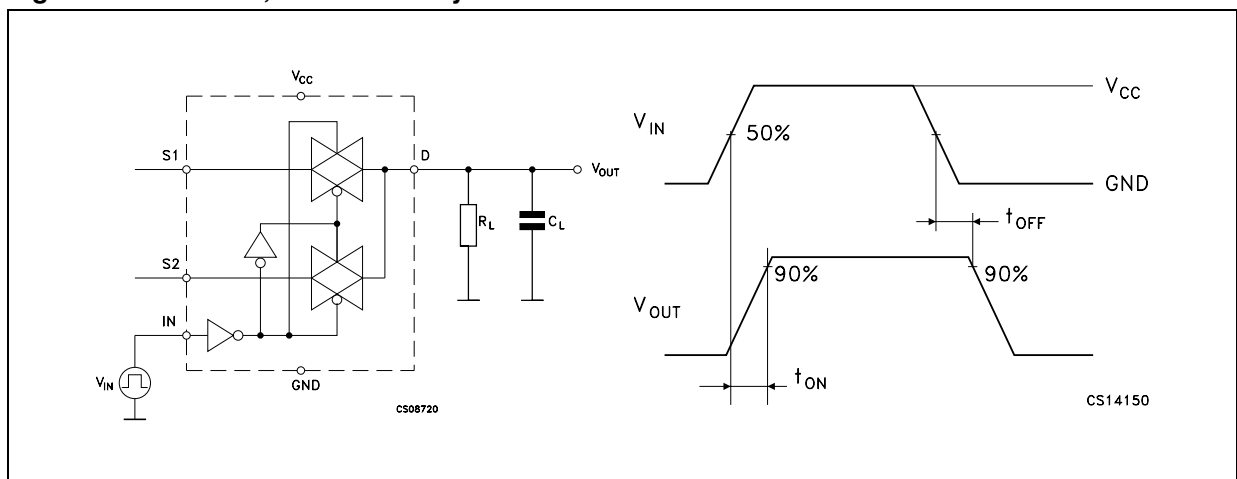


Figure 12. Turn ON, turn OFF delay time



6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 13. Package outline for Flip-chip 12 (1.9 x 1.4 x 0.58 mm) - 0.50 mm pitch

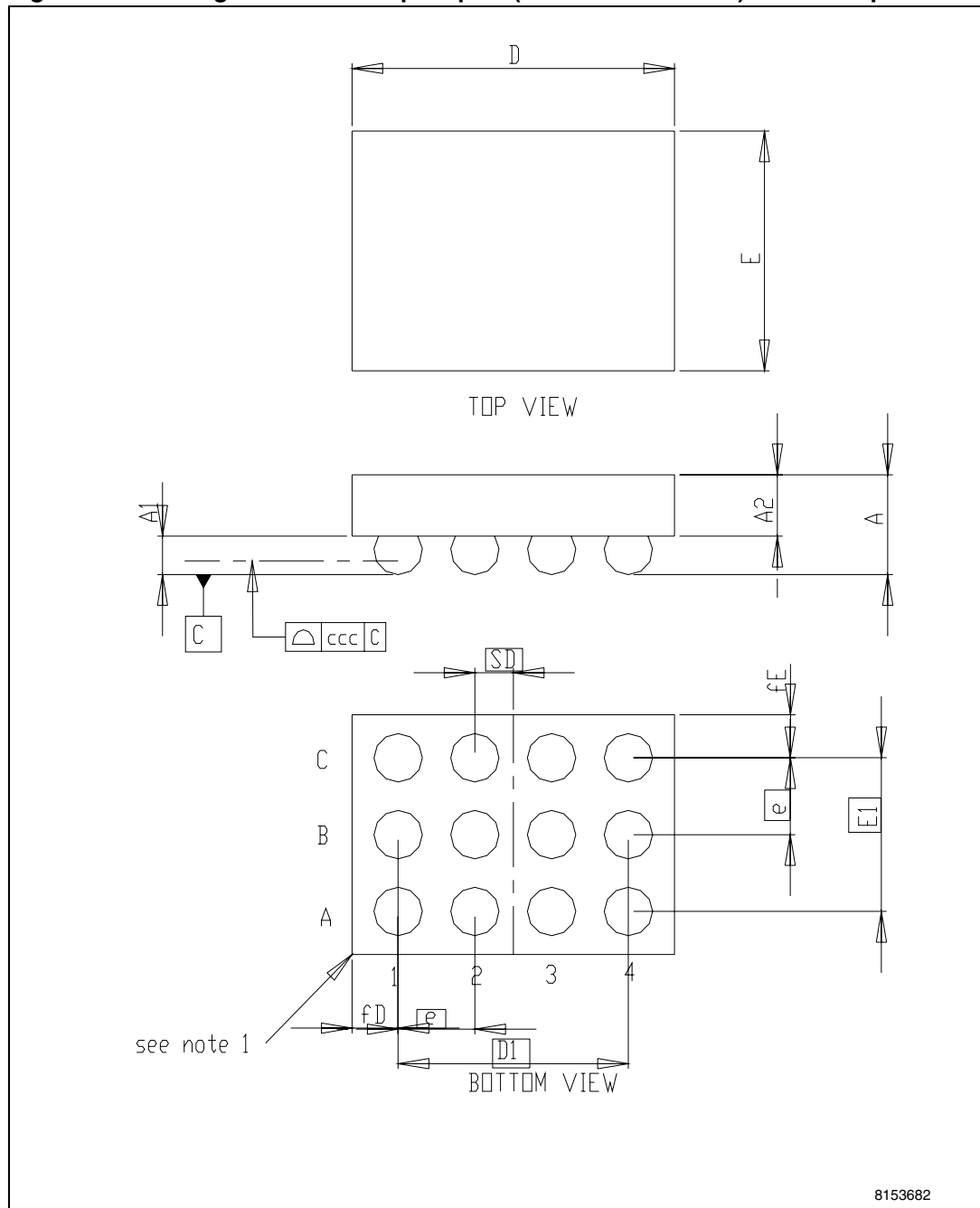
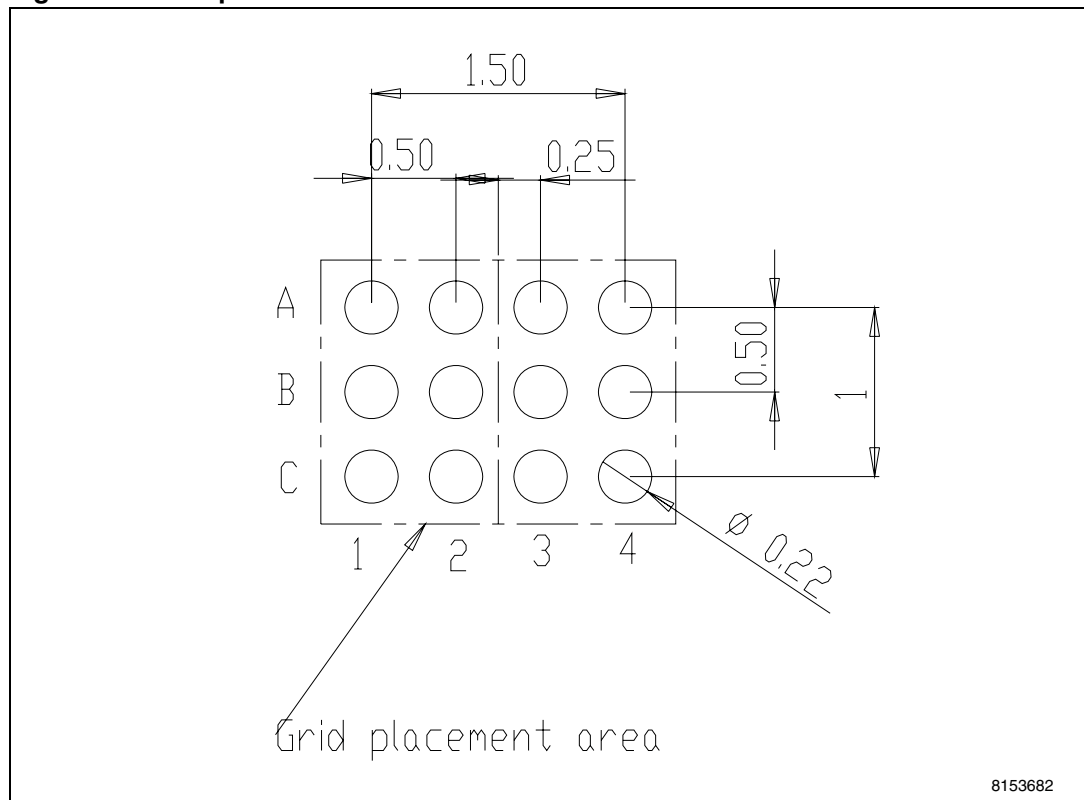


Table 9. Mechanical data for Flip-chip 12 (1.9 x 1.4 x 0.58 mm) - 0.50 mm pitch

Symbol	Millimeters		
	Min	Typ	Max
A	0.535	0.58	0.625
A1	0.18	0.205	0.23
A2	0.355	0.375	0.395
b	0.215	0.255	0.295
D	1.85	1.9	1.95
D1	-	1.5	-
e	0.45	0.5	0.55
E	1.35	1.4	1.45
E1	-	1	-
SD	-	0.25	-
f	0.19	0.2	0.21
ccc	-	0.08	-

Figure 14. Footprint recommendation



8153682

Figure 15. Tape information for Flip-chip 12 (1.9 x 1.4 x 0.58 mm) - 0.50 mm pitch

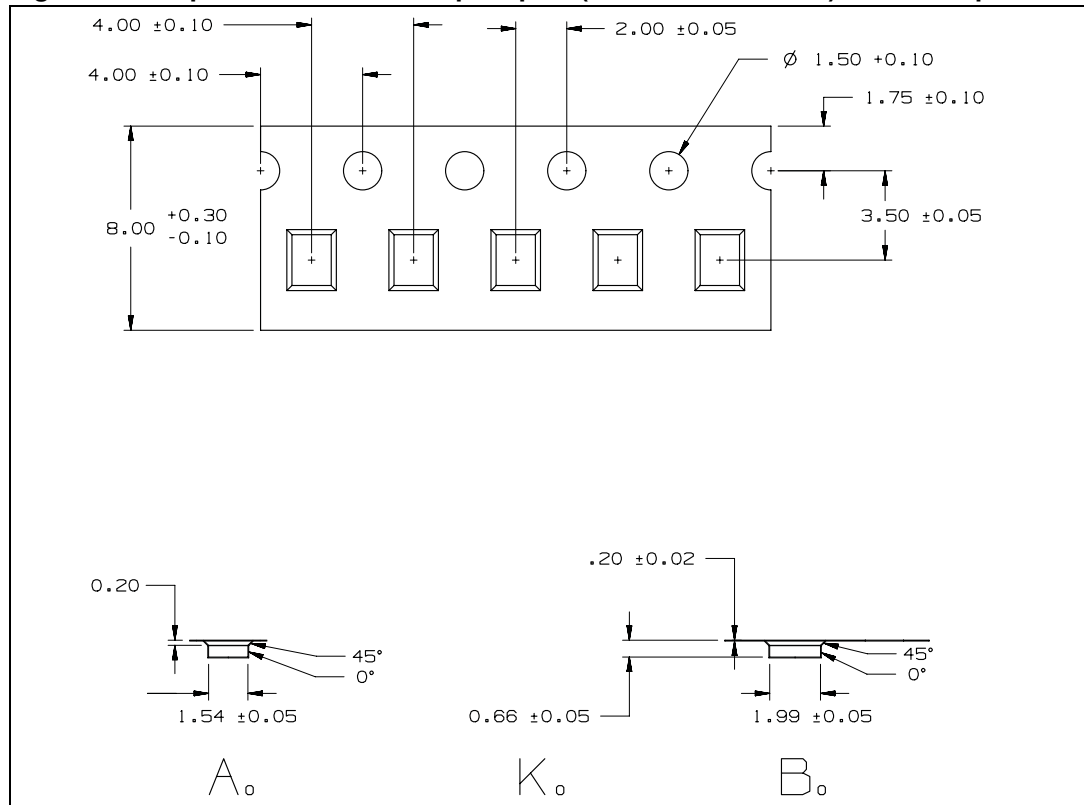
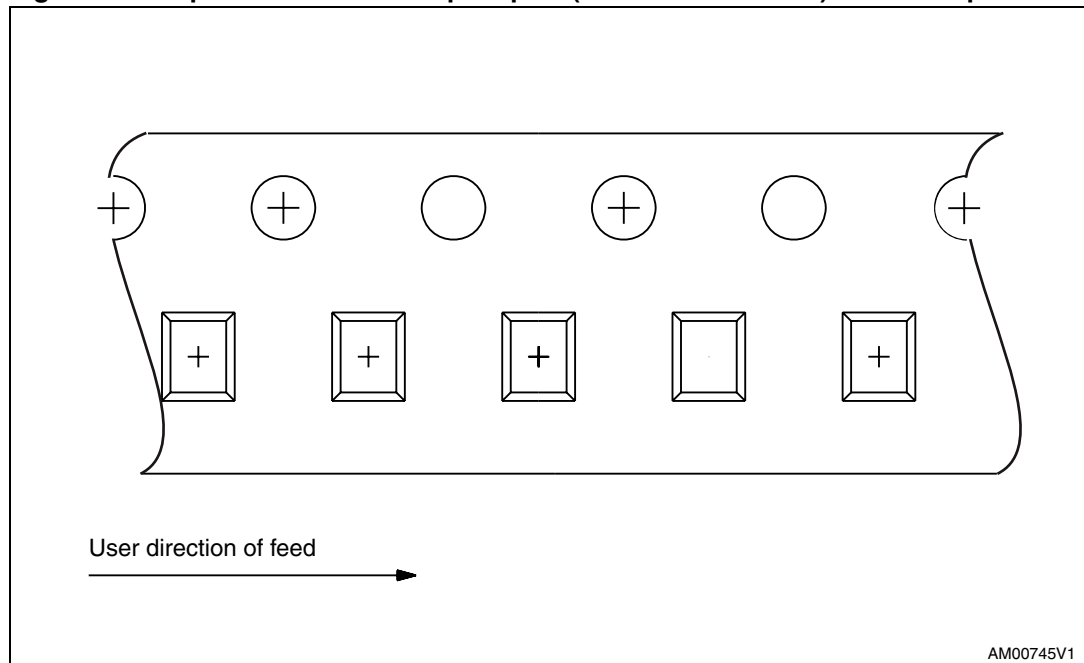


Figure 16. Tape orientation for Flip-chip 12 (1.9 x 1.4 x 0.58 mm) - 0.50 mm pitch



AM00745V1

7 Revision history

Table 10. Document revision history

Date	Revision	Changes
19-Nov-2008	1	Initial release.
20-Apr-2009	2	Document status promoted from preliminary data to datasheet. Modified: Table 6: DC specifications on page 6 and Section 6 .

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2009 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com